

# PMV33UPE

20 V, single P-channel Trench MOSFET



## 1. Product profile

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- 2 kV ESD protected

### 1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-20	V
$V_{GS}$	gate-source voltage		-8	-	8	V
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	-5.3	A
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -3\text{ A}; T_j = 25\text{ °C}$	-	30	36	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<p>SOT23 (TO-236AB)</p>	<p>017aaa259</p>
2	S	source		
3	D	drain		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV33UPE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMV33UPE	EJ%

[1] % = placeholder for manufacturing site code

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### 5. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-20	V	
$V_{GS}$	gate-source voltage		-8	8	V	
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	-5.3	A
		$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-4.4	A
		$V_{GS} = -4.5\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	-2.8	A
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$	-	-17.6	A	
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	490	mW
			[1]	-	980	mW
		$T_{sp} = 25\text{ °C}$		-	4150	mW
$T_j$	junction temperature		-55	150	°C	
$T_{amb}$	ambient temperature		-55	150	°C	
$T_{stg}$	storage temperature		-65	150	°C	

#### Source-drain diode

$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	-1.2	A
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#### ESD maximum rating

$V_{ESD}$	electrostatic discharge voltage	HBM	[3]	-	2000	V
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[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

### 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	222	255	K/W
			[2]	-	111	128	K/W
			[3]	-	74	85	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	25	30	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>,  $t \leq 5\text{ s}$ .

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## 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	-0.45	-0.7	-0.95	V
$I_{DSS}$	drain leakage current	$V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
		$V_{DS} = -20 V; V_{GS} = 0 V; T_j = 150 \text{ }^\circ C$	-	-	-15	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
		$V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -4.5 V; I_D = -3 A; T_j = 25 \text{ }^\circ C$	-	30	36	m $\Omega$
		$V_{GS} = -4.5 V; I_D = -3 A; T_j = 150 \text{ }^\circ C$	-	43	51	m $\Omega$
		$V_{GS} = -2.5 V; I_D = -3 A; T_j = 25 \text{ }^\circ C$	-	38	47	m $\Omega$
		$V_{GS} = -1.8 V; I_D = -3 A; T_j = 25 \text{ }^\circ C$	-	51	65	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = -10 V; I_D = -4.4 A; T_j = 25 \text{ }^\circ C$	-	16	-	S
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -10 V; I_D = -4.4 A; V_{GS} = -4.5 V; T_j = 25 \text{ }^\circ C$	-	14.7	22.1	nC
$Q_{GS}$	gate-source charge		-	2.6	-	nC
$Q_{GD}$	gate-drain charge		-	2.5	-	nC
$C_{iss}$	input capacitance	$V_{DS} = -10 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	1820	-	pF
$C_{oss}$	output capacitance		-	208	-	pF
$C_{rss}$	reverse transfer capacitance		-	146	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -10 V; I_D = -4.4 A; V_{GS} = -4.5 V; R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^\circ C$	-	11	-	ns
$t_r$	rise time		-	30	-	ns
$t_{d(off)}$	turn-off delay time		-	83	-	ns
$t_f$	fall time		-	39	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = -1.2 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-0.7	-1.2	V